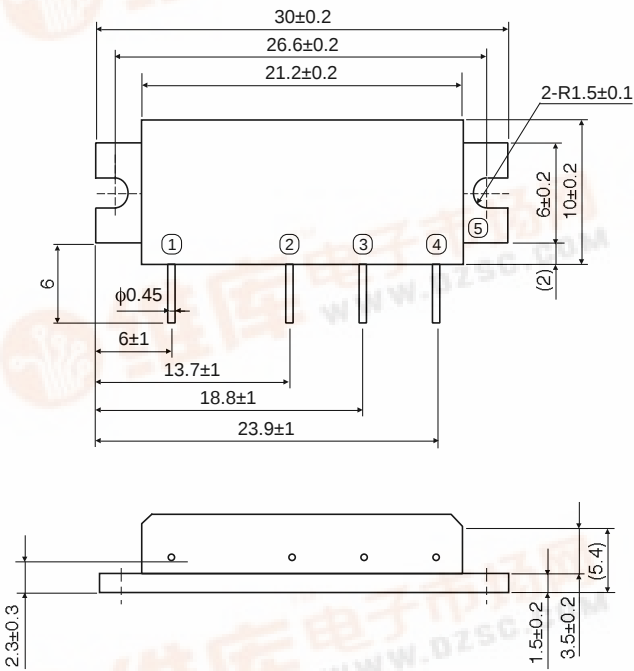
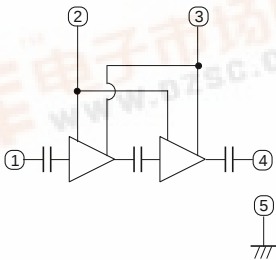


OUTLINE DRAWING

Dimensions in mm



BLOCK DIAGRAM



PIN:

- ①Pin : RF INPUT
- ②VGG : GATE BIAS SUPPLY
- ③VDD : DRAIN BIAS SUPPLY
- ④Po : RF OUTPUT
- ⑤GND: FIN

ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
VDD	Supply voltage	VGG£3.5V, ZG=ZL=50W	9.2	V
VGG	Gate bias voltage		4	V
Pin	Input power	f=142-163MHz, ZG=ZL=50W	70	mW
Po	Output power	f=142-163MHz, ZG=ZL=50W	10	W
Tc (OP)	Operation case temperature	f=142-163MHz, ZG=ZL=50W	-30 to +100	°C
Tstg	Storage temperature		-40 to +110	°C

Note. Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS (Tc=25°C, ZG=ZL=50W unless otherwise noted)

Symbol	Parameter	Test conditions	Limits		Unit
			Min	Max	
f	Frequency range		142	163	MHz
Po	Output power	VDD=7.2V, VGG=3.5V, Pin=50W	7		W
hT	Total efficiency		45		%
2fo	2nd. harmonic			-20	dBc
r in	Input VSWR			4	-
-	Stability	ZG=50W, VDD=4-9.2V, Load VSWR<4:1	No parasitic oscillation		-
-	Load VSWR tolerance	VDD=9.2V, Pin=50mW, Po=7W (VGG adjust), ZL=20:1	No degradation or destroy		-

Note. Above parameters, ratings, limits and test conditions are subject to change.

SILICON MOS FET POWER AMPLIFIER, 142-163MHz, 7W, FM PORTABLE RADIO

TYPICAL PERFORMANCE DATA

